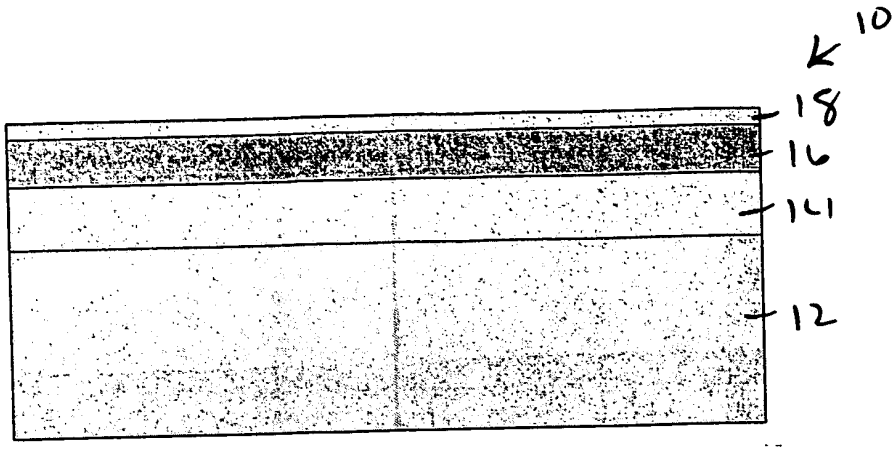

FIG. 1

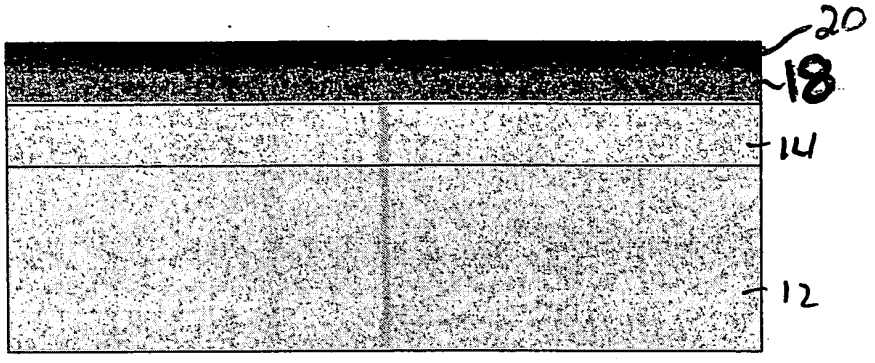

FIG. 2

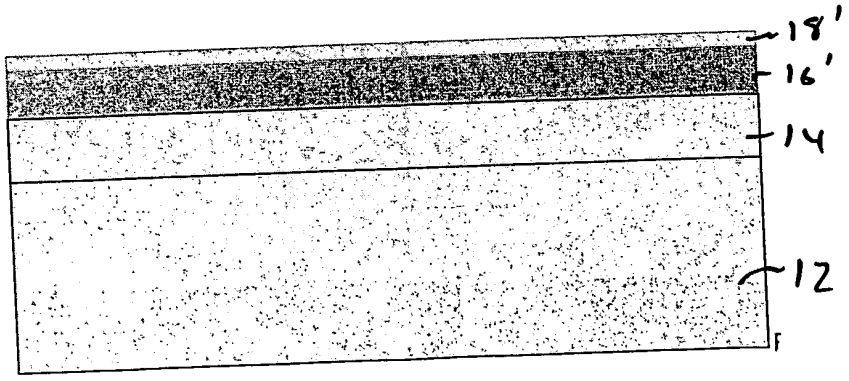

FIG 3

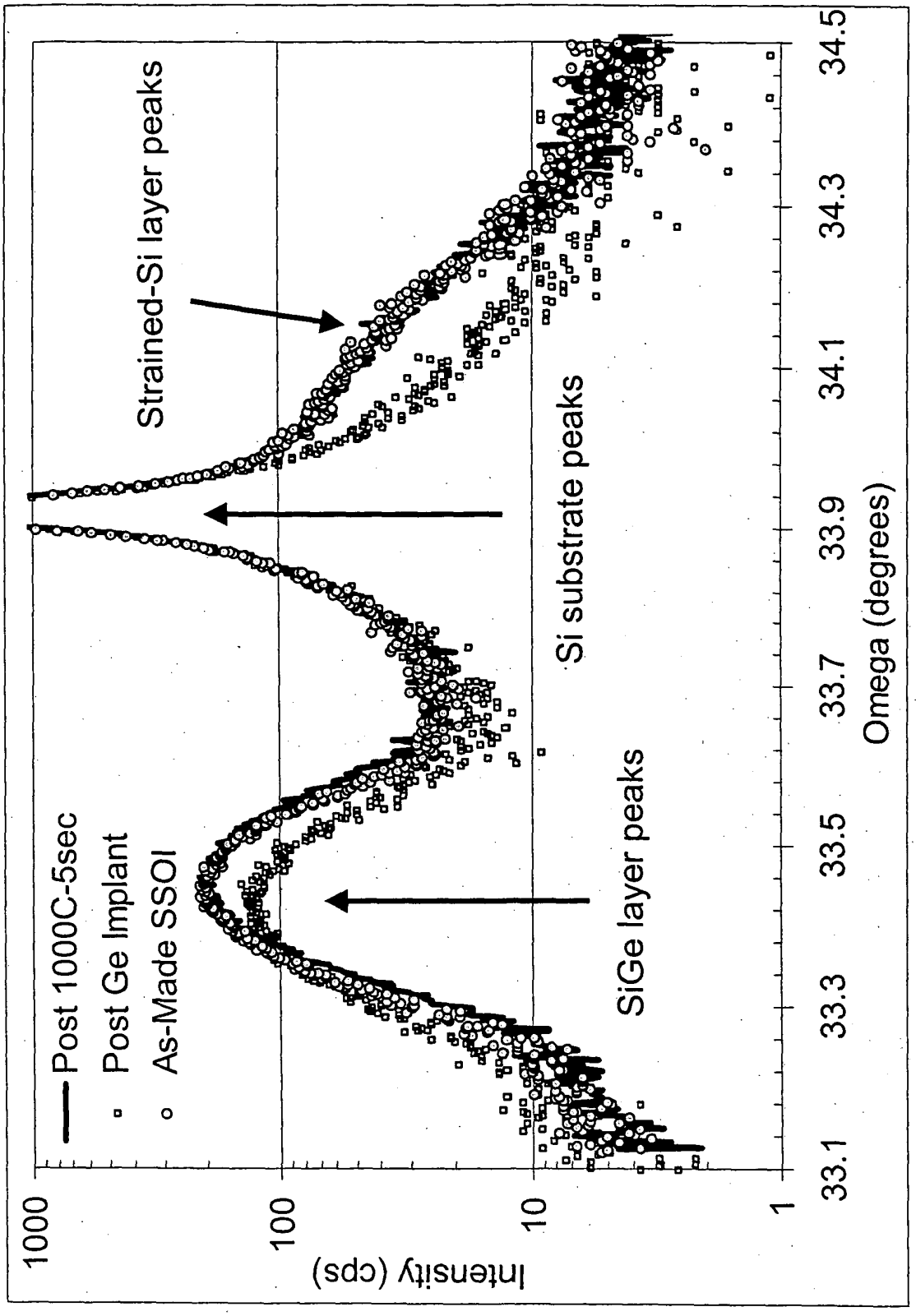
Post 1000C-5sec
Post Ge Implant
As-Made SSOI
Strained-Si layer peaks
Si substrate peaks
SiGe layer peaks
Intensity (cps)
1000
100
10
1
33.1
33.3
33.5
33.7
33.9
34.1
34.3
34.5
Omega (degrees)

FIG. 4

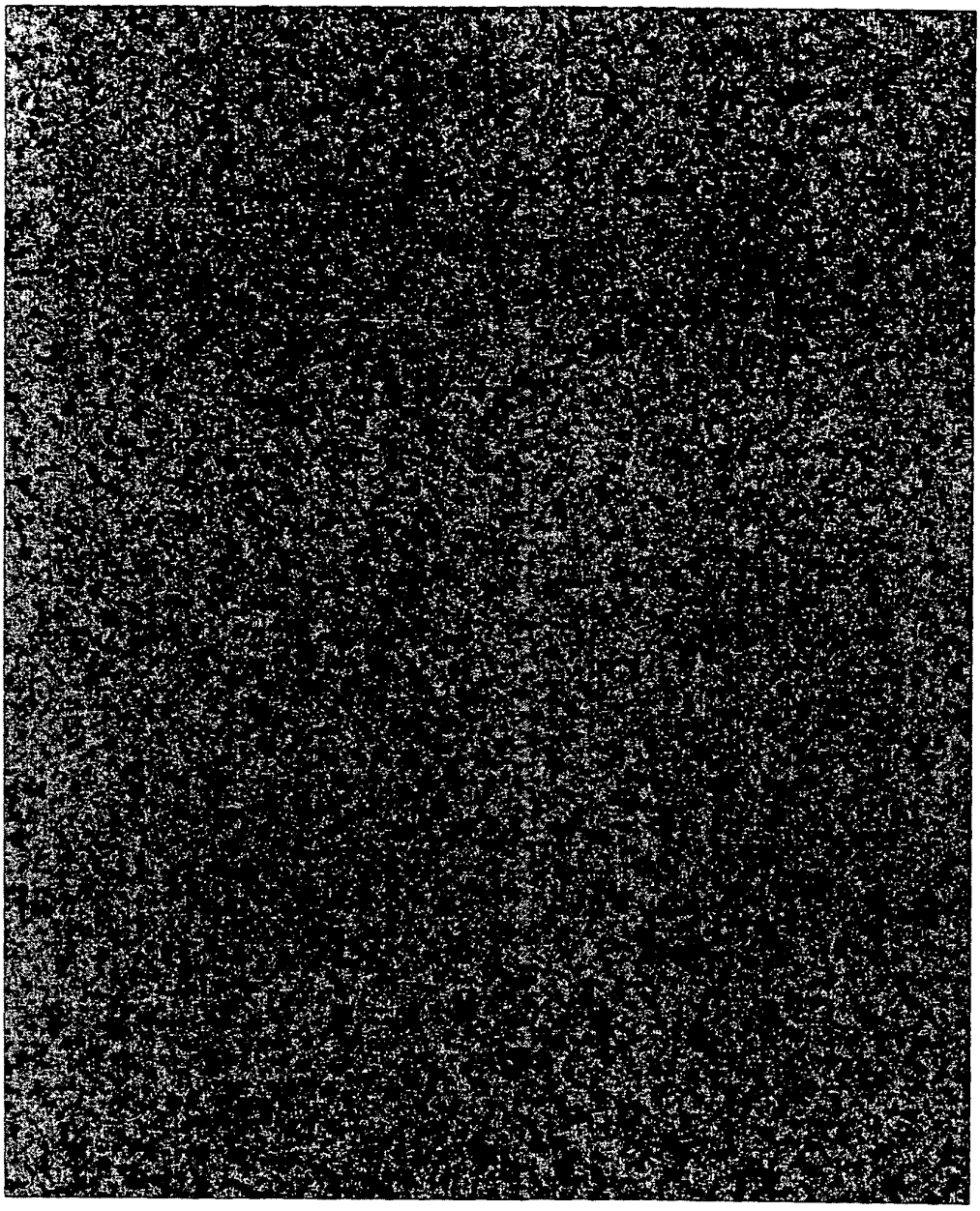

FIG. 5

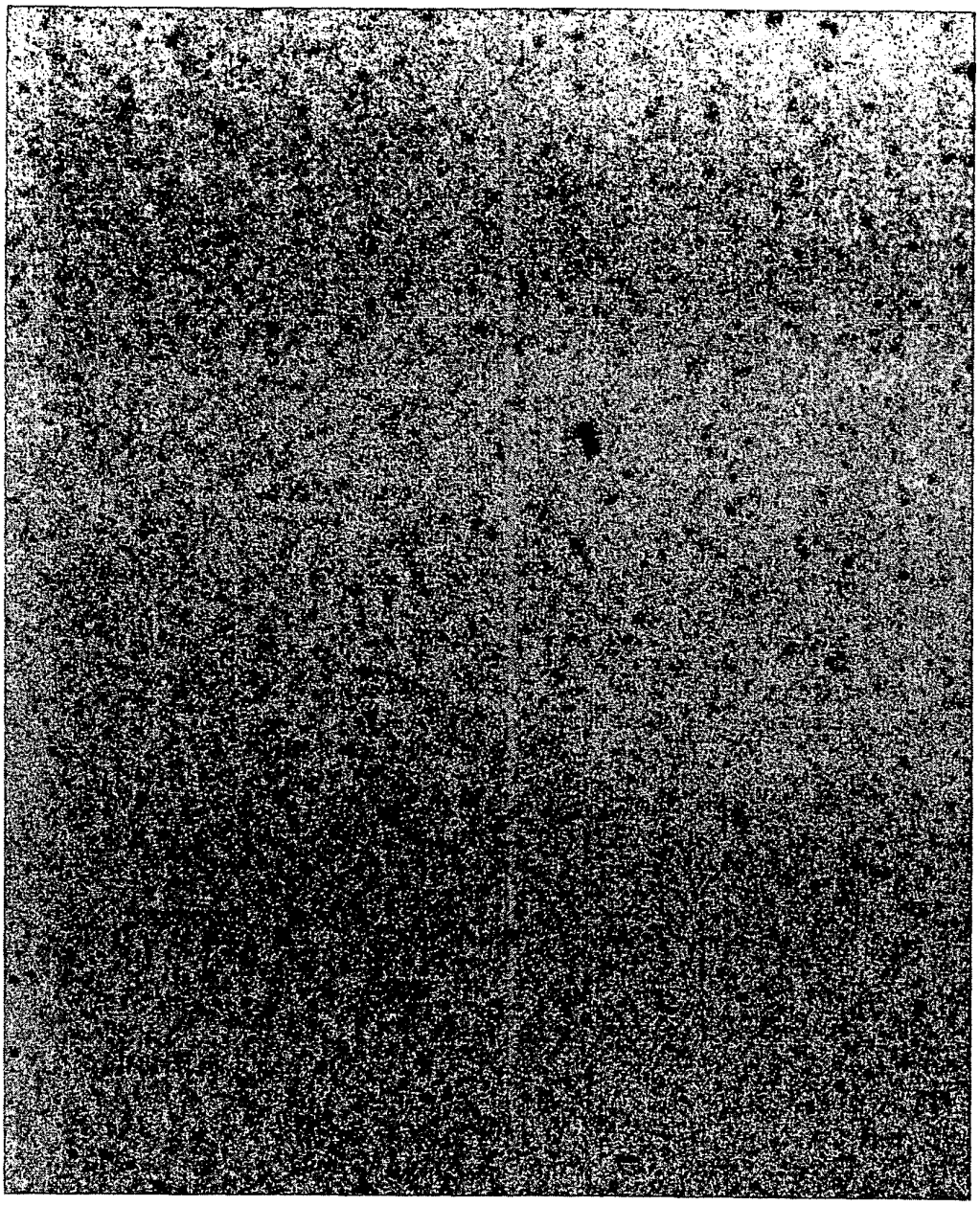

FIG. 6